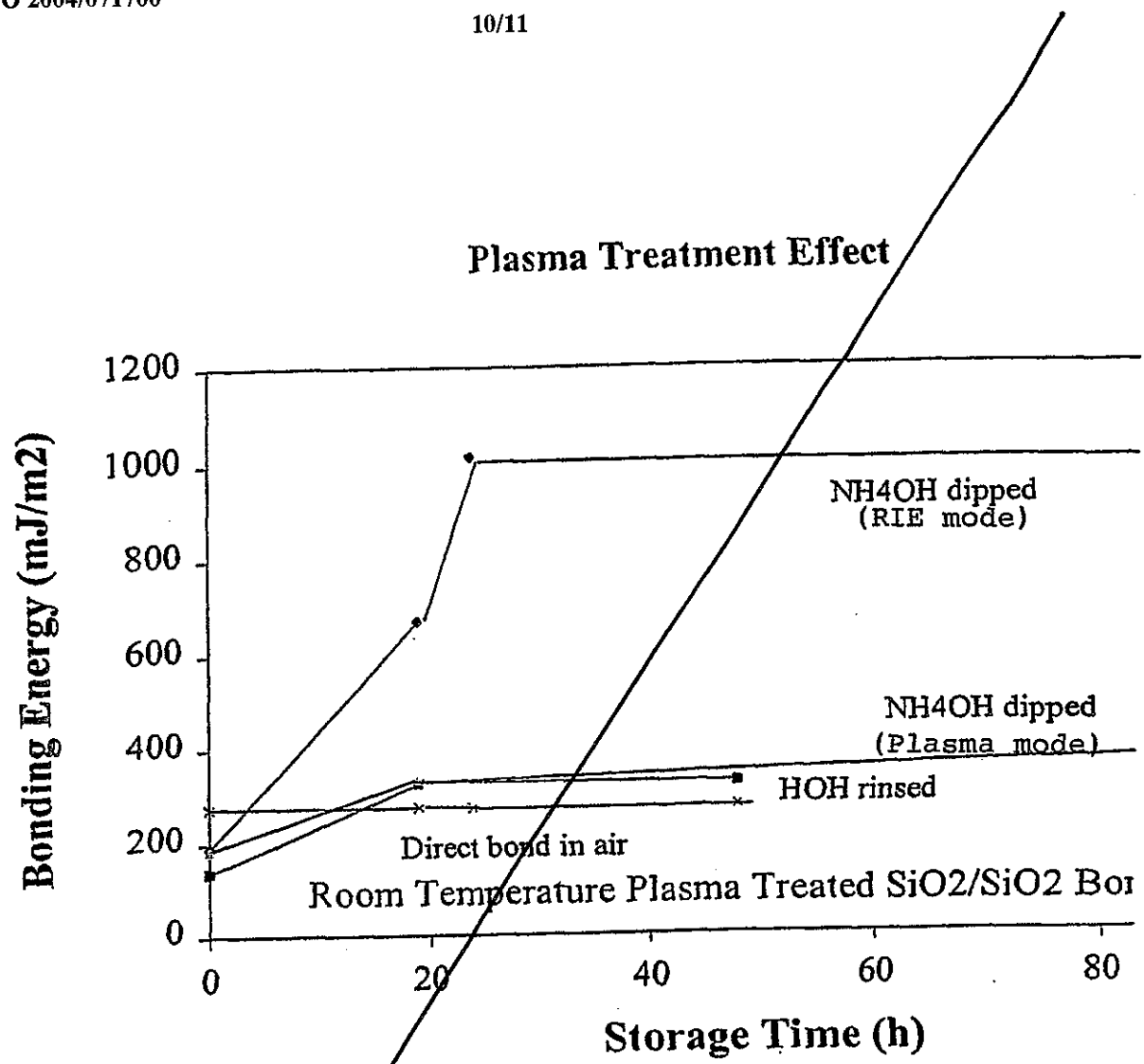

Plasma Treatment Effect
Bonding Energy (mJ/m2)
1200
1000
800
600
400
200
0
0
20
40
60
80
Storage Time (h)
NH4OH dipped
(RIE mode)
NH4OH dipped
(Plasma mode)
HOH rinsed
Direct bond in air
Room Temperature Plasma Treated SiO2/SiO2 Bo

FIG. 8

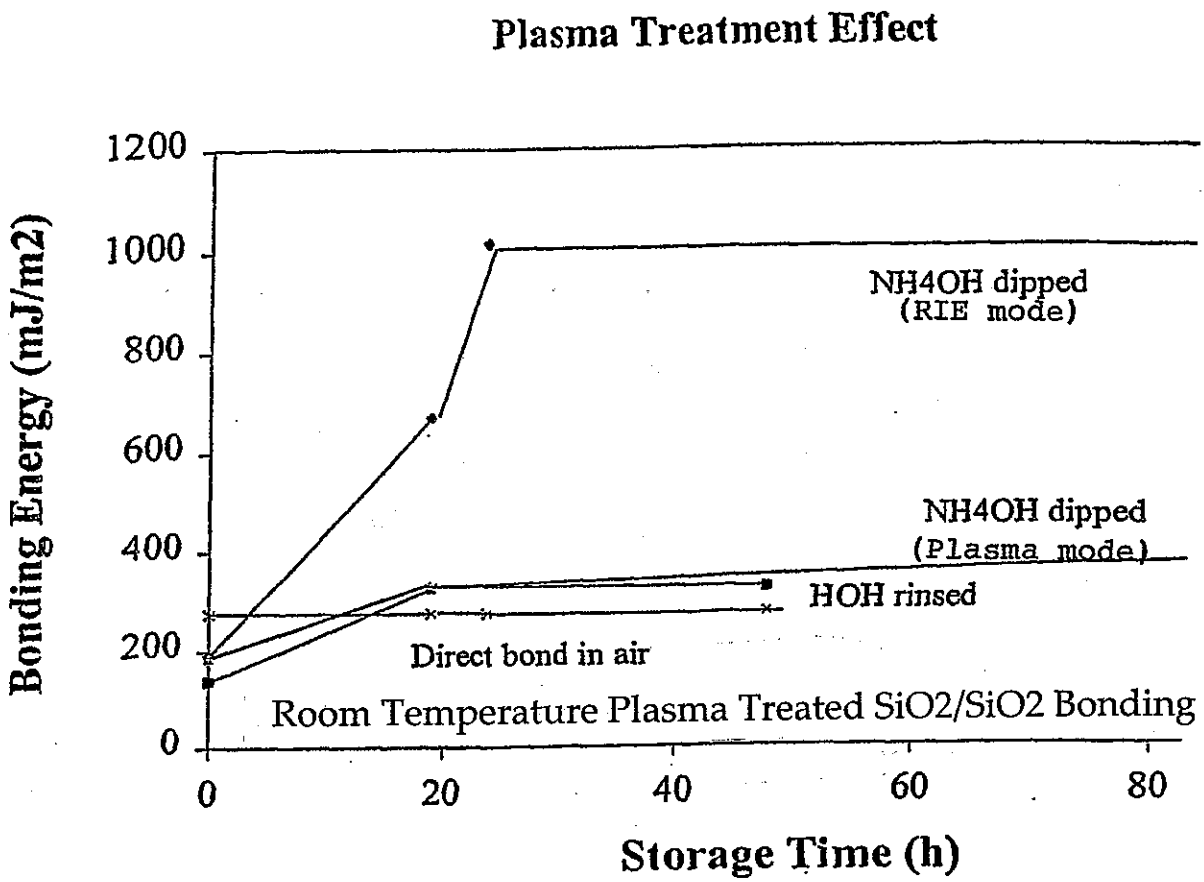

Plasma Treatment Effect
Bonding Energy (mJ/m2)
1200
1000
800
600
400
200
0
0
20
40
60
80
Storage Time (h)
NH4OH dipped
(RIE mode)
NH4OH dipped
(Plasma mode)
HOH rinsed
Direct bond in air
Room Temperature Plasma Treated SiO2/SiO2 Bonding

FIG. 8